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FEATURES

- Operate With 3-V to 5.5-V V_{CC} Supply
- · Operate up to 1 Mbit/s
- Low Supply Current . . . 300 μA Typ
- External Capacitors . . . $4 \times 0.1 \mu F$
- Accept 5-V Logic Input With 3.3-V Supply
- Latch-Up Performance Exceeds 100 mA Per JESD 78, Class II
- ESD Protection for RS-232 Pins
 - ±15-kV Human-Body Model (HBM)
 - ±15-kV IEC 61000-4-2 Air-Gap Discharge
 - ±8-kV IEC 61000-4-2 Contact Discharge

APPLICATIONS

- Battery-Powered Systems
- PDAs
- Notebooks
- Laptops
- Palmtop PCs
- Hand-Held Equipment

D, DB, DW, OR PW PACKAGE (TOP VIEW) 16 V_{CC} V+ **∏** 2 15**∏** GND C1- [] 3 14∏ DOUT1 C2+ **∏** 4 13 RIN1 C2- [] 5 12 ROUT1 V− **∏** 6 11 ∏ DIN1 DOUT2 7 10 DIN2 RIN2 8 9 ROUT2

DESCRIPTION/ORDERING INFORMATION

The SN65C3232E and SN75C3232E consist of two line drivers, two line receivers, and a dual charge-pump circuit with ± 15 -kV ESD protection pin to pin (serial-port connection pins, including GND). These devices provide the electrical interface between an asynchronous communication controller and the serial-port connector. The charge pump and four small external capacitors allow operation from a single 3-V to 5.5-V supply. The devices operate at data signaling rates up to 1 Mbit/s and a driver output slew rate of 14 V/ μ s to 150 V/ μ s.

ORDERING INFORMATION

T _A	PACK	AGE ⁽¹⁾⁽²⁾	ORDERABLE PART NUMBER	TOP-SIDE MARKING
	SOIC - D	Tube of 40	SN65C3232ED	65C3232E
	3010 - D	Reel of 2500	SN65C3232EDR	00C3Z3ZE
	SOIC - DW	Tube of 40	SN65C3232EDW	6FC2222F
–40°C to 85°C	201C - DW	Reel of 2000	SN65C3232EDWR	65C3232E
	SSOP – DB	Reel of 2000	SN65C3232EDBR	MU232E
	TSSOP – PW	Tube of 90	SN65C3232EPW	MU232E
		Reel of 2000	SN65C3232EPWR	WU232E
	SOIC - D	Tube of 40	SN75C3232ED	75000005
	201C - D	Reel of 2500	SN75C3232EDR	75C3232E
	SOIC - DW	Tube of 40	SN75C3232EDW	75C3232E
0°C to 70°C	201C - DW	Reel of 2000	SN75C3232EDWR	75U3Z3ZE
	SSOP – DB	Reel of 2000	SN75C3232EDBR	MY232E
	TCCOD DW	Tube of 90	SN75C3232EPW	MV222F
	TSSOP – PW	Reel of 2000	SN75C3232EPWR	MY232E

⁽¹⁾ Package drawings, thermal data, and symbolization are available at www.ti.com/packaging.

⁽²⁾ For the most current package and ordering information, see the Package Option Addendum at the end of this document, or see the TI website at www ti com.



Please be aware that an important notice concerning availability, standard warranty, and use in critical applications of Texas Instruments semiconductor products and disclaimers thereto appears at the end of this data sheet.



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Table 1. 1-Mbit/s RS-232 Parts

TEMPERATURE RANGE	PART NO.	NO. OF DRIVERS	NO. OF RECEIVERS	ESD	SUPPLY V _{CC} (V)	FEATURE	PIN/PACKAGE
	SN65C3221E	1	1	±15-kV Air-Gap, ±8-kV Contact, ±15-kV HBM	3.3 or 5	Auto powerdown	16-pin SOIC, SSOP, TSSOP
	SN65C3232E	2	2	±15-kV Air-Gap, ±8-kV Contact, ±15-kV HBM	3.3 or 5	Low pin count	16-pin SOIC, SSOP, TSSOP
	MAX3227I	1	1	±8-kV Air-Gap, ±8-kV Contact, ±15-kV HBM	3.3 or 5	Auto powerdown plus, ready signal	16-pin SSOP
–40°C to 85°C	SN65C3221	1	1	±15-kV HBM	3.3 or 5	Auto powerdown	16-pin SOIC, SSOP, TSSOP
	SN65C3223	2	2	±15-kV HBM	3.3 or 5	Auto powerdown, enable signal	20-pin SOIC, SSOP, TSSOP
	SN65C3222	2	2	±15-kV HBM	3.3 or 5	Enable, powerdown signal	20-pin SOIC, SSOP, TSSOP
	SN65C3232	2	2	±15-kV HBM	3.3 or 5	Low pin count	16-pin SOIC, SSOP, TSSOP
	SN65C3238	5	3	±15-kV HBM	3.3 or 5	Auto powerdown plus	28-pin SOIC, SSOP, TSSOP
	SN65C3243	3	5	±15-kV HBM	3.3 or 5	Auto powerdown	28-pin SOIC, SSOP, TSSOP
	SN75C3221E	1	1	±15-kV Air-Gap, ±8-kV Contact, ±15-kV HBM	3.3 or 5	Auto powerdown	16-pin SOIC, SSOP, TSSOP
	SN75C3232E	2	2	±15-kV Air-Gap, ±8-kV Contact, ±15-kV HBM	3.3 or 5	Low pin count	16-pin SOIC, SSOP, TSSOP
	MAX3227C	1	1	±8-kV Air-Gap, ±8-kV Contact, ±15-kV HBM	3.3 or 5	Auto powerdown plus, ready signal	16-pin SSOP
0°C to 70°C	SN75C3221	1	1	±15-kV HBM	3.3 or 5	Auto powerdown	16-pin SOIC, SSOP, TSSOP
	SN75C3223	2	2	±15-kV HBM	3.5 or 5	Auto powerdown, enable signal	20-pin SOIC, SSOP, TSSOP
	SN75C3222	2	2	±15-kV HBM	3.3 or 5	Enable, powerdown signal	20-pin SOIC, SSOP, TSSOP
	SN75C3232	2	2	±15-kV HBM	3.3 or 5	Low pin count	16-pin SOIC, SSOP, TSSOP
	SN75C3238	5	3	±15-kV HBM	3.3 or 5	Auto powerdown plus	28-pin SOIC, SSOP, TSSOP
	SN75C3243	3	5	±15-kV HBM	3.3 or 5	Auto powerdown	28-pin SOIC, SSOP, TSSOP

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FUNCTION TABLES

EACH DRIVER(1)

INPUT DIN	OUTPUT DOUT
L	Н
Н	L

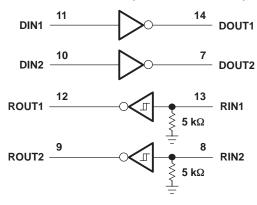
(1) H = high level, L = low level

EACH RECEIVER (1)

INPUT RIN	OUTPUT ROUT
L	Н
Н	L
Open	Н

(1) H = high level, L = low level, Open = input disconnected or connected driver off

LOGIC DIAGRAM (POSITIVE LOGIC)



TEXAS INSTRUMENTS

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Absolute Maximum Ratings(1)

over operating free-air temperature range (unless otherwise noted)

			MIN	MAX	UNIT
V _{CC}	Supply voltage range (2)		-0.3	6	V
V+	Positive output supply voltage range ⁽²⁾		-0.3	7	V
V-	Negative output supply voltage range ⁽²⁾		0.3	-7	V
V+ - V-	Supply voltage difference ⁽²⁾	pply voltage difference ⁽²⁾		13	V
VI	lanut valta na na na	Drivers	-0.3	6	V
	Input voltage range	Receivers	-25	25	V
	Output voltage range	Drivers	-13.2	13.2	V
Vo		Receivers	-0.3	$V_{CC} + 0.3$	V
		D package		82	
0	Package thermal impedance (3)(4)	DB package		46	°C/W
θ_{JA}	Package thermal impedance (57.5)	DW package		57	-C/VV
		PW package		108	
T _J	Operating virtual junction temperature	,		150	°C
T _{stg}	Storage temperature range		-65	150	°C

⁽¹⁾ Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

Recommended Operating Conditions⁽¹⁾

				MIN	NOM	MAX	UNIT
	Supply voltage		V _{CC} = 3.3 V	3	3.3	3.6	V
			V _{CC} = 5 V	4.5	5	5.5	V
\/	Driver high-level input voltage	DIN	V _{CC} = 3.3 V	2			V
V _{IH}		DIN	$V_{CC} = 5 V$	2.4			v
V_{IL}	Driver low-level input voltage		DIN			0.8	V
\/	Driver input voltage DIN		DIN	0		5.5	V
VI	Receiver input voltage			-25		25	V
_	Operating free cir temperature		SN65C3232E	-40		85	°C
T _A	Operating free-air temperature		SN75C3232E	0		70	٠.

⁽¹⁾ Test conditions are C1–C4 = 0.1 μ F at V_{CC} = 3.3 V \pm 0.3 V; C1 = 0.047 μ F, C2–C4 = 0.33 μ F at V_{CC} = 5 V \pm 0.5 V (see Figure 4).

Electrical Characteristics(1)

over recommended ranges of supply voltage and operating free-air temperature (unless otherwise noted)

PARAMETER		TEST CONDITIONS		MIN	TYP ⁽²⁾	MAX	UNIT
I _{CC}	Supply current	No load,	V_{CC} = 3.3 V or 5 V		0.3	1	mA

⁽¹⁾ Test conditions are C1–C4 = 0.1 μ F at V_{CC} = 3.3 V ± 0.3 V; C1 = 0.047 μ F, C2–C4 = 0.33 μ F at V_{CC} = 5 V ± 0.5 V (see Figure 4).

⁽²⁾ All voltages are with respect to network GND.

⁽³⁾ Maximum power dissipation is a function of $T_J(max)$, θ_{JA} , and T_A . The maximum allowable power dissipation at any allowable ambient temperature is $P_D = (T_J(max) - T_A)/\theta_{JA}$. Operating at the absolute maximum T_J of 150°C can affect reliability.

⁽⁴⁾ The package thermal impedance is calculated in accordance with JESD 51-7.

⁽²⁾ All typical values are at $V_{CC} = 3.3 \text{ V}$ or $V_{CC} = 5 \text{ V}$, and $T_A = 25^{\circ}\text{C}$.

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DRIVER SECTION

Electrical Characteristics(1)

over recommended ranges of supply voltage and operating free-air temperature (unless otherwise noted)

PARAMETER		TEST CONDITIONS		MIN	TYP ⁽²⁾	MAX	UNIT
V_{OH}	High-level output voltage	DOUT at $R_L = 3 \text{ k}\Omega$ to GND,	DIN = GND	5	5.5		V
V _{OL}	Low-level output voltage	DOUT at $R_L = 3 \text{ k}\Omega$ to GND,	DIN = V _{CC}	-5	-5.4		V
I_{IH}	High-level input current	$V_I = V_{CC}$			±0.01	±1	μΑ
I _{IL}	Low-level input current	V _I at GND			±0.01	±1	μΑ
(3)	Chart aircuit autout aurrant	V _{CC} = 3.6 V,	V _O = 0 V		±35	±60	A
I _{OS} (3)	Short-circuit output current	V _{CC} = 5.5 V,	V _O = 0 V		±35	±90	mA
r _o	Output resistance	V_{CC} , V+, and V- = 0 V,	V _O = ±2 V	300	10M		Ω

Test conditions are C1–C4 = 0.1 μ F at V_{CC} = 3.3 V ± 0.3 V; C1 = 0.047 μ F, C2–C4 = 0.33 μ F at V_{CC} = 5 V ± 0.5 V (see Figure 4) .

Switching Characteristics⁽¹⁾

over recommended ranges of supply voltage and operating free-air temperature (unless otherwise noted)

	PARAMETER TEST CONDITIONS			MIN	TYP ⁽²⁾	MAX	UNIT
	Maximum data rate	$R_L = 3 k\Omega$,	$C_L = 250 \text{ pF}, \qquad V_{CC} = 3 \text{ V to } 4.5 \text{ V}$	1000			kbit/s
	(see Figure 1) One DOUT swit	One DOUT switching	$C_L = 1000 \text{ pF}, \qquad V_{CC} = 3.5 \text{ V to } 5.5 \text{ V}$	1000			KDII/S
t _{sk(p)}	Pulse skew ⁽³⁾	$C_L = 150 \text{ pF to } 2500 \text{ pF, } R_L$	$_{L}$ = 150 pF to 2500 pF, R $_{L}$ = 3 kΩ to 7 kΩ, See Figure 2		300		ns
SR(tr)	Slew rate, transition region (see Figure 1)	$R_L = 3 \text{ k}\Omega \text{ to } 7 \text{ k}\Omega, C_L = 150$	$_{L}$ = 3 k Ω to 7 k Ω , C_{L} = 150 pF to 1000 pF, V_{CC} = 3.3 V			150	V/μs

Test conditions are C1–C4 = 0.1 μ F at V_{CC} = 3.3 V \pm 0.3 V; C1 = 0.047 μ F, C2–C4 = 0.33 μ F at V_{CC} = 5 V \pm 0.5 V (see Figure 4). All typical values are at V_{CC} = 3.3 V or V_{CC} = 5 V, and T_A = 25°C.

ESD Protection

TERM	IINAL	TEST CONDITIONS		UNIT
NAME	NO.	TEST CONDITIONS	TYP	UNIT
		НВМ	±15	
DOUT	7, 14	IEC 61000-4-2 Air-Gap Discharge	±15	kV
		IEC 61000-4-2 Contact Discharge	±8	

All typical values are at $V_{CC} = 3.3 \text{ V}$ or $V_{CC} = 5 \text{ V}$, and $T_A = 25^{\circ}\text{C}$. Short-circuit durations should be controlled to prevent exceeding the device absolute power dissipation ratings, and not more than one output should be shorted at a time.

Pulse skew is defined as |t_{PLH} - t_{PHL}| of each channel of the same device.

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RECEIVER SECTION

Electrical Characteristics(1)

over recommended ranges of supply voltage and operating free-air temperature (unless otherwise noted)

	PARAMETER	TEST CONDITIONS	MIN	TYP ⁽²⁾	MAX	UNIT
V_{OH}	High-level output voltage	$I_{OH} = -1 \text{ mA}$	V _{CC} - 0.6	V _{CC} - 0.1		V
V_{OL}	Low-level output voltage	I _{OL} = 1.6 mA			0.4	V
V	Positive-going input threshold voltage	$V_{CC} = 3.3 \text{ V}$		1.5	2.4	V
V _{IT+}		$V_{CC} = 5 V$		1.8	2.4	V
V	Negative-going input threshold voltage	$V_{CC} = 3.3 \text{ V}$	0.6	1.2		V
V _{IT}		V _{CC} = 5 V	0.8	1.5		V
V _{hys}	Input hysteresis (V _{IT+} – V _{IT-})			0.3		V
ri	Input resistance	$V_I = \pm 3 \text{ V to } \pm 25 \text{ V}$	3	5	7	kΩ

⁽¹⁾ Test conditions are C1–C4 = 0.1 μ F at V_{CC} = 3.3 V \pm 0.3 V; C1 = 0.047 μ F, C2–C4 = 0.33 μ F at V_{CC} = 5 V \pm 0.5 V (see Figure 4). (2) All typical values are at V_{CC} = 3.3 V or V_{CC} = 5 V, and T_A = 25°C.

Switching Characteristics(1)

over recommended ranges of supply voltage and operating free-air temperature (unless otherwise noted)

	PARAMETER	TEST CONDITIONS	TYP ⁽²⁾	UNIT
t _{PLH}	Propagation delay time, low- to high-level output	C 150 pF	300	ns
t _{PHL}	Propagation delay time, high- to low-level output	$C_L = 150 \text{ pF}$	300	ns
t _{sk(p)}	Pulse skew ⁽³⁾		300	ns

⁽¹⁾ Test conditions are C1–C4 = 0.1 μ F at V_{CC} = 3.3 V \pm 0.3 V; C1 = 0.047 μ F, C2–C4 = 0.33 μ F at V_{CC} = 5 V \pm 0.5 V (see Figure 4). (2) All typical values are at V_{CC} = 3.3 V or V_{CC} = 5 V, and T_A = 25°C.

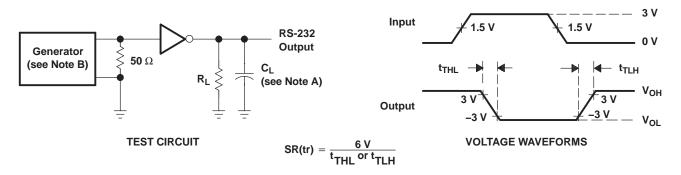
ESD Protection

TERMINAL		TEST CONDITIONS	TYP	LINUT
NAME	NO.	TEST CONDITIONS	ITP	UNIT
		НВМ	±15	
RIN	8, 13	IEC 61000-4-2 Air-Gap Discharge	±15	kV
		IEC 61000-4-2 Contact Discharge	±8	

Pulse skew is defined as |t_{PLH} - t_{PHL}| of each channel of the same device.

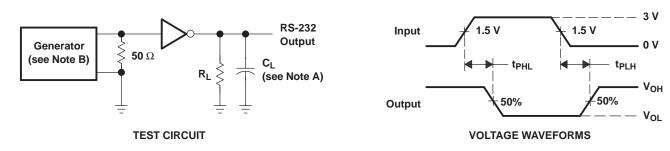


PARAMETER MEASUREMENT INFORMATION



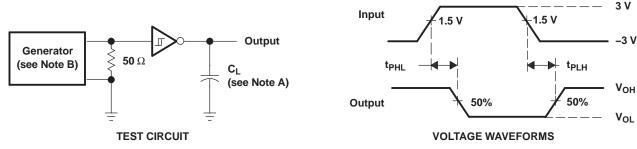
- NOTES: A. C_L includes probe and jig capacitance.
 - B. The pulse generator has the following characteristics: PRR = 250 kbit/s, $Z_0 = 50 \Omega$, 50% duty cycle, $t_f \le 10$ ns. $t_f \le 10$ ns.

Figure 1. Driver Slew Rate



- NOTES: A. C_L includes probe and jig capacitance.
 - B. The pulse generator has the following characteristics: PRR = 250 kbit/s, Z_0 = 50 Ω , 50% duty cycle, $t_r \le 10$ ns. $t_f \le 10$ ns.

Figure 2. Driver Pulse Skew

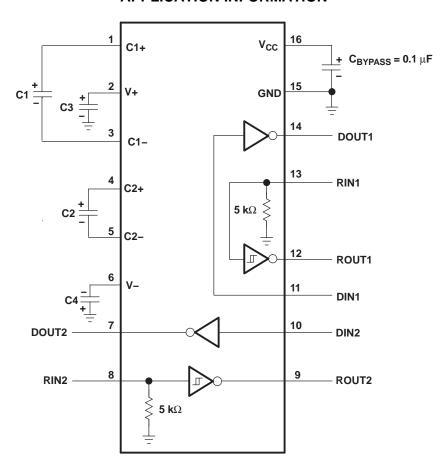


- NOTES: A. C_L includes probe and jig capacitance.
 - B. The pulse generator has the following characteristics: $Z_O = 50~\Omega$, 50% duty cycle, $t_f \le 10$ ns. $t_f \le 10$ ns.

Figure 3. Receiver Propagation Delay Times



APPLICATION INFORMATION



V_{CC} vs CAPACITOR VALUES

V _{CC}	C1	C2, C3, C4
$\begin{array}{c} 3.3 \text{ V} \pm 0.3 \text{ V} \\ 5 \text{ V} \pm 0.5 \text{ V} \\ 3 \text{ V to } 5.5 \text{ V} \end{array}$	0.1 μF 0.047 μF 0.1 μF	0.1 μF 0.33 μF 0.47 μF

A. C3 can be connected to V_{CC} or GND.

Figure 4. Typical Operating Circuit and Capacitor Values



PACKAGING INFORMATION

Orderable Device	Status ⁽¹⁾	Package Type	Package Drawing	Pins	Package Qty	e Eco Plan ⁽²⁾	Lead/Ball Finish	MSL Peak Temp ⁽³⁾
SN65C3232ED	ACTIVE	SOIC	D	16	40	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM
SN65C3232EDB	ACTIVE	SSOP	DB	16	80	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM
SN65C3232EDBG4	ACTIVE	SSOP	DB	16	80	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM
SN65C3232EDBR	ACTIVE	SSOP	DB	16	2000	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM
SN65C3232EDBRG4	ACTIVE	SSOP	DB	16	2000	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM
SN65C3232EDE4	ACTIVE	SOIC	D	16	40	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM
SN65C3232EDG4	ACTIVE	SOIC	D	16	40	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM
SN65C3232EDR	ACTIVE	SOIC	D	16	2500	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM
SN65C3232EDRE4	ACTIVE	SOIC	D	16	2500	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM
SN65C3232EDRG4	ACTIVE	SOIC	D	16	2500	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM
SN65C3232EDW	ACTIVE	SOIC	DW	16	40	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM
SN65C3232EDWG4	ACTIVE	SOIC	DW	16	40	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM
SN65C3232EDWR	ACTIVE	SOIC	DW	16	2000	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM
SN65C3232EDWRG4	ACTIVE	SOIC	DW	16	2000	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM
SN65C3232EPW	ACTIVE	TSSOP	PW	16	90	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM
SN65C3232EPWE4	ACTIVE	TSSOP	PW	16	90	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM
SN65C3232EPWG4	ACTIVE	TSSOP	PW	16	90	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM
SN65C3232EPWR	ACTIVE	TSSOP	PW	16	2000	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM
SN65C3232EPWRE4	ACTIVE	TSSOP	PW	16	2000	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM
SN65C3232EPWRG4	ACTIVE	TSSOP	PW	16	2000	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM
SN75C3232ED	ACTIVE	SOIC	D	16	40	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM
SN75C3232EDB	ACTIVE	SSOP	DB	16	80	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM
SN75C3232EDBG4	ACTIVE	SSOP	DB	16	80	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM
SN75C3232EDBR	ACTIVE	SSOP	DB	16	2000	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM
SN75C3232EDBRG4	ACTIVE	SSOP	DB	16	2000	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM





com 28-Nov-2007

Orderable Device	Status ⁽¹⁾	Package Type	Package Drawing	Pins	Packag Qty	e Eco Plan ⁽²⁾	Lead/Ball Finish	MSL Peak Temp ⁽³⁾
SN75C3232EDE4	ACTIVE	SOIC	D	16	40	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM
SN75C3232EDG4	ACTIVE	SOIC	D	16	40	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM
SN75C3232EDR	ACTIVE	SOIC	D	16	2500	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM
SN75C3232EDRE4	ACTIVE	SOIC	D	16	2500	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM
SN75C3232EDRG4	ACTIVE	SOIC	D	16	2500	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM
SN75C3232EDW	ACTIVE	SOIC	DW	16	40	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM
SN75C3232EDWG4	ACTIVE	SOIC	DW	16	40	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM
SN75C3232EDWR	ACTIVE	SOIC	DW	16	2000	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM
SN75C3232EDWRG4	ACTIVE	SOIC	DW	16	2000	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM
SN75C3232EPW	ACTIVE	TSSOP	PW	16	90	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM
SN75C3232EPWE4	ACTIVE	TSSOP	PW	16	90	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM
SN75C3232EPWG4	ACTIVE	TSSOP	PW	16	90	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM
SN75C3232EPWR	ACTIVE	TSSOP	PW	16	2000	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM
SN75C3232EPWRE4	ACTIVE	TSSOP	PW	16	2000	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM
SN75C3232EPWRG4	ACTIVE	TSSOP	PW	16	2000	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM

⁽¹⁾ The marketing status values are defined as follows:

ACTIVE: Product device recommended for new designs.

LIFEBUY: TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.

NRND: Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.

PREVIEW: Device has been announced but is not in production. Samples may or may not be available.

OBSOLETE: TI has discontinued the production of the device.

(2) Eco Plan - The planned eco-friendly classification: Pb-Free (RoHS), Pb-Free (RoHS Exempt), or Green (RoHS & no Sb/Br) - please check http://www.ti.com/productcontent for the latest availability information and additional product content details.

TBD: The Pb-Free/Green conversion plan has not been defined.

Pb-Free (RoHS): TI's terms "Lead-Free" or "Pb-Free" mean semiconductor products that are compatible with the current RoHS requirements for all 6 substances, including the requirement that lead not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, TI Pb-Free products are suitable for use in specified lead-free processes.

Pb-Free (RoHS Exempt): This component has a RoHS exemption for either 1) lead-based flip-chip solder bumps used between the die and package, or 2) lead-based die adhesive used between the die and leadframe. The component is otherwise considered Pb-Free (RoHS compatible) as defined above.

Green (RoHS & no Sb/Br): TI defines "Green" to mean Pb-Free (RoHS compatible), and free of Bromine (Br) and Antimony (Sb) based flame retardants (Br or Sb do not exceed 0.1% by weight in homogeneous material)

(3) MSL, Peak Temp. -- The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.

Important Information and Disclaimer: The information provided on this page represents TI's knowledge and belief as of the date that it is



PACKAGE OPTION ADDENDUM

28-Nov-2007

provided. TI bases its knowledge and belief on information provided by third parties, and makes no representation or warranty as to the accuracy of such information. Efforts are underway to better integrate information from third parties. TI has taken and continues to take reasonable steps to provide representative and accurate information but may not have conducted destructive testing or chemical analysis on incoming materials and chemicals. TI and TI suppliers consider certain information to be proprietary, and thus CAS numbers and other limited information may not be available for release.

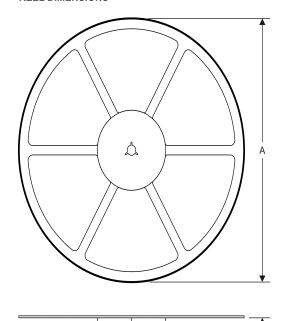
In no event shall TI's liability arising out of such information exceed the total purchase price of the TI part(s) at issue in this document sold by TI to Customer on an annual basis.

PACKAGE MATERIALS INFORMATION

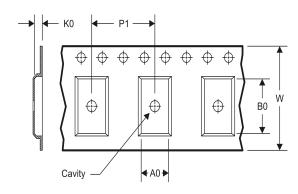
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TAPE AND REEL INFORMATION

REEL DIMENSIONS



TAPE DIMENSIONS



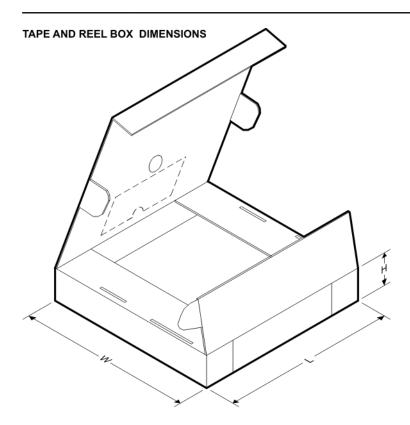
A0	Dimension designed to accommodate the component width
В0	Dimension designed to accommodate the component length
K0	Dimension designed to accommodate the component thickness
W	Overall width of the carrier tape
P1	Pitch between successive cavity centers

TAPE AND REEL INFORMATION

*All dimensions are nominal

Device	Package Type	Package Drawing		SPQ	Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
SN65C3232EDBR	SSOP	DB	16	2000	330.0	16.4	8.2	6.6	2.5	12.0	16.0	Q1
SN65C3232EDR	SOIC	D	16	2500	330.0	16.4	6.5	10.3	2.1	8.0	16.0	Q1
SN65C3232EDWR	SOIC	DW	16	2000	330.0	16.4	10.75	10.7	2.7	12.0	16.0	Q1
SN65C3232EPWR	TSSOP	PW	16	2000	330.0	12.4	6.9	5.6	1.6	8.0	12.0	Q1
SN75C3232EDBR	SSOP	DB	16	2000	330.0	16.4	8.2	6.6	2.5	12.0	16.0	Q1
SN75C3232EDR	SOIC	D	16	2500	330.0	16.4	6.5	10.3	2.1	8.0	16.0	Q1
SN75C3232EDWR	SOIC	DW	16	2000	330.0	16.4	10.75	10.7	2.7	12.0	16.0	Q1
SN75C3232EPWR	TSSOP	PW	16	2000	330.0	12.4	6.9	5.6	1.6	8.0	12.0	Q1

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*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Length (mm)	Width (mm)	Height (mm)
SN65C3232EDBR	SSOP	DB	16	2000	367.0	367.0	38.0
SN65C3232EDR	SOIC	D	16	2500	367.0	367.0	38.0
SN65C3232EDWR	SOIC	DW	16	2000	367.0	367.0	38.0
SN65C3232EPWR	TSSOP	PW	16	2000	367.0	367.0	35.0
SN75C3232EDBR	SSOP	DB	16	2000	367.0	367.0	38.0
SN75C3232EDR	SOIC	D	16	2500	367.0	367.0	38.0
SN75C3232EDWR	SOIC	DW	16	2000	367.0	367.0	38.0
SN75C3232EPWR	TSSOP	PW	16	2000	367.0	367.0	35.0

D (R-PDS0-G16)

PLASTIC SMALL OUTLINE

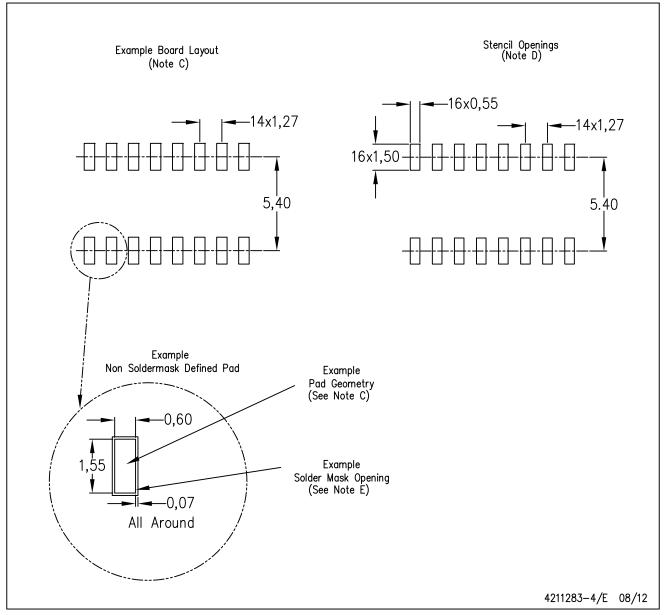


- A. All linear dimensions are in inches (millimeters).
- B. This drawing is subject to change without notice.
- Body length does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not exceed 0.006 (0,15) each side.
- Body width does not include interlead flash. Interlead flash shall not exceed 0.017 (0,43) each side.
- E. Reference JEDEC MS-012 variation AC.



D (R-PDSO-G16)

PLASTIC SMALL OUTLINE

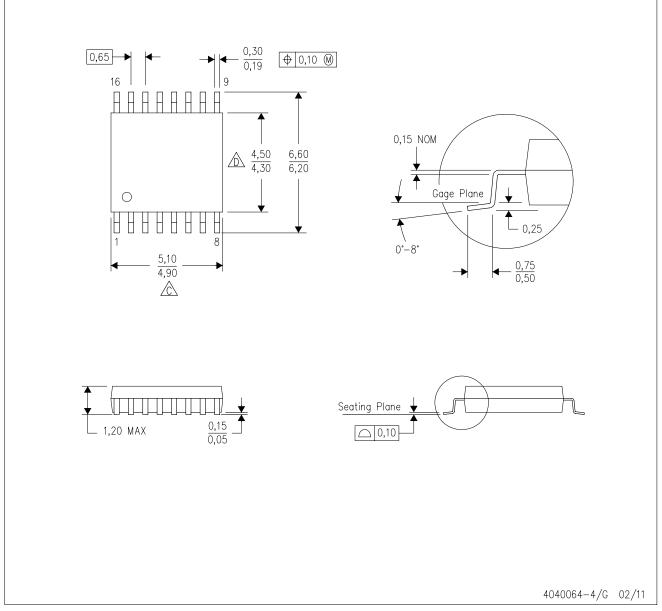


- A. All linear dimensions are in millimeters.
- B. This drawing is subject to change without notice.
- C. Publication IPC-7351 is recommended for alternate designs.
- D. Laser cutting apertures with trapezoidal walls and also rounding corners will offer better paste release. Customers should contact their board assembly site for stencil design recommendations. Refer to IPC-7525 for other stencil recommendations.
- E. Customers should contact their board fabrication site for solder mask tolerances between and around signal pads.



PW (R-PDSO-G16)

PLASTIC SMALL OUTLINE

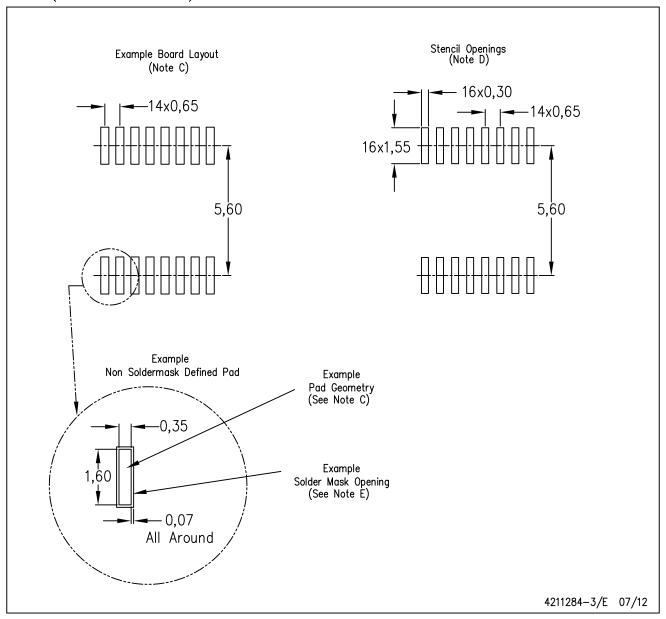


- A. All linear dimensions are in millimeters. Dimensioning and tolerancing per ASME Y14.5M—1994.
- B. This drawing is subject to change without notice.
- Body length does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not exceed 0,15 each side.
- Body width does not include interlead flash. Interlead flash shall not exceed 0,25 each side.
- E. Falls within JEDEC MO-153



PW (R-PDSO-G16)

PLASTIC SMALL OUTLINE

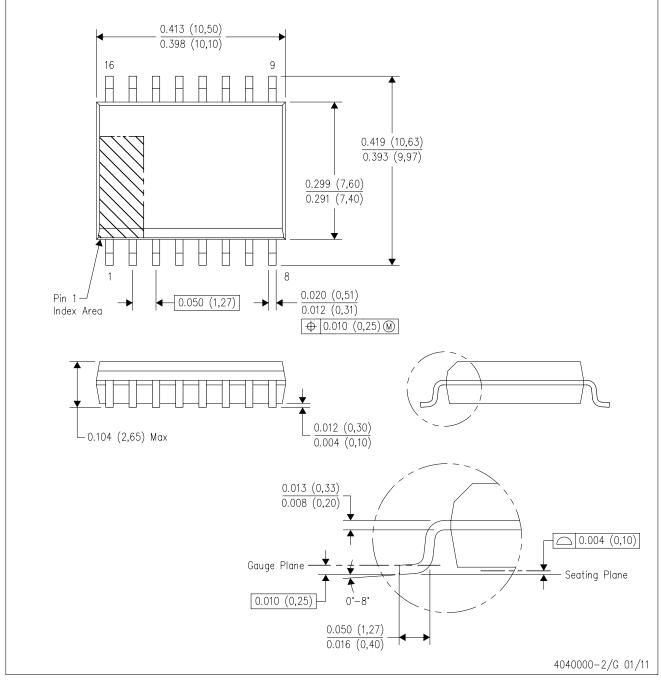


- A. All linear dimensions are in millimeters.
- B. This drawing is subject to change without notice.
- C. Publication IPC-7351 is recommended for alternate designs.
- D. Laser cutting apertures with trapezoidal walls and also rounding corners will offer better paste release. Customers should contact their board assembly site for stencil design recommendations. Refer to IPC-7525 for other stencil recommendations.
- E. Customers should contact their board fabrication site for solder mask tolerances between and around signal pads.



DW (R-PDSO-G16)

PLASTIC SMALL OUTLINE



NOTES: A. All linear dimensions are in inches (millimeters). Dimensioning and tolerancing per ASME Y14.5M-1994.

- B. This drawing is subject to change without notice.
- C. Body dimensions do not include mold flash or protrusion not to exceed 0.006 (0,15).
- D. Falls within JEDEC MS-013 variation AA.



DB (R-PDSO-G**)

PLASTIC SMALL-OUTLINE

28 PINS SHOWN



NOTES: A. All linear dimensions are in millimeters.

B. This drawing is subject to change without notice.

C. Body dimensions do not include mold flash or protrusion not to exceed 0,15.

D. Falls within JEDEC MO-150

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